SOT223 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

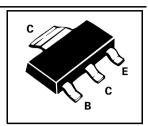
FZT560

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FEATURES

- * 500 Volt V_{CEO}
- * 150mA continuous current
- * P_{tot} = 2 Watt

PARTMARKING DETAIL - FZT560



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-500	٧
Collector-Emitter Voltage	V _{CEO}	-500	٧
Emitter-Base Voltage	V_{EBO}	-5	٧
Peak Pulse Current	I _{CM}	-500	mA
Continuous Collector Current	I _C	-150	mA
Power Dissipation at T _{amb} =25°C	P _{tot}	2	W
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-500		V	I _C =-100μA
Collector-Emitter Breakdown Voltage	V _{CEO(SUS)}	-500		V	I _C =-10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5		V	I _E =-100μA
Collector Cut-Off Current	I _{CBO}		-100	nA	V _{CB} =-500V
Collector Cut-Off Current	I _{CES}		-100	nA	V _{CE} =-500V
Emitter Cut-Off Current	I _{EBO}		-100	nA	V _{EB} =-5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.20 -0.5	V V	I _C =-20mA, I _B =-2mA I _C =-50mA, I _B =-10mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}		-0.9	V	I _C =-50mA, I _B =-10mA*
Base-Emitter Turn On Voltage	V _{BE(on)}		-0.9	V	I _C =-50mA, V _{CE} =-10V*
Static Forward Current Transfer Ratio	h _{FE}	100 80 15 typ	300 300		I _C =-1mA, V _{CE} =-10V I _C =-50mA, V _{CE} =-10V* I _C =-100mA, V _{CE} =-10V*
Transition Frequency	f _T	60		MHz	I _C =-10mA, V _{CE} =-20V f=50MHz
Output Capacitance	C _{obo}		8	pF	V _{CB} =-20, f=1MHz
Switching times	t _{on} t _{off}	110 typ 1.5 typ).	ns μs	V _{CE} =-100, I _C =-50mA, I _{B1} =-5mA,I _{B2} =10mA,

^{*} Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%

FZT560

TYPICAL CHARACTERISTICS

